

512 Kbit (64Kb x 8) NMOS UV EPROM

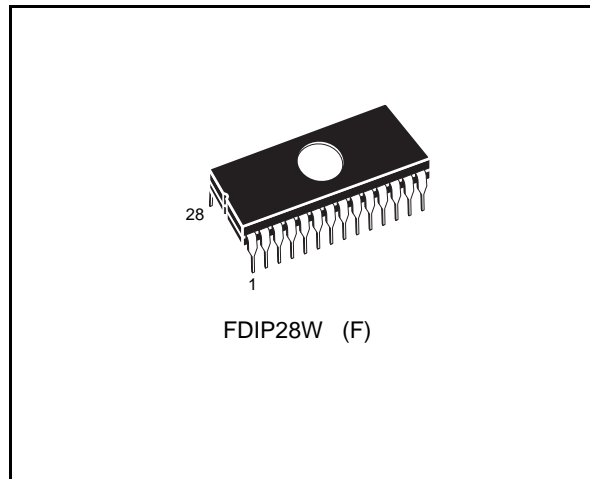
DATA BRIEFING

- FAST ACCESS TIME: 200ns
- EXTENDED TEMPERATURE RANGE
- SINGLE 5V SUPPLY VOLTAGE
- LOW STANDBY CURRENT: 40mA max
- TTL COMPATIBLE DURING READ and PROGRAM
- FAST PROGRAMMING ALGORITHM
- ELECTRONIC SIGNATURE
- PROGRAMMING VOLTAGE: 12V

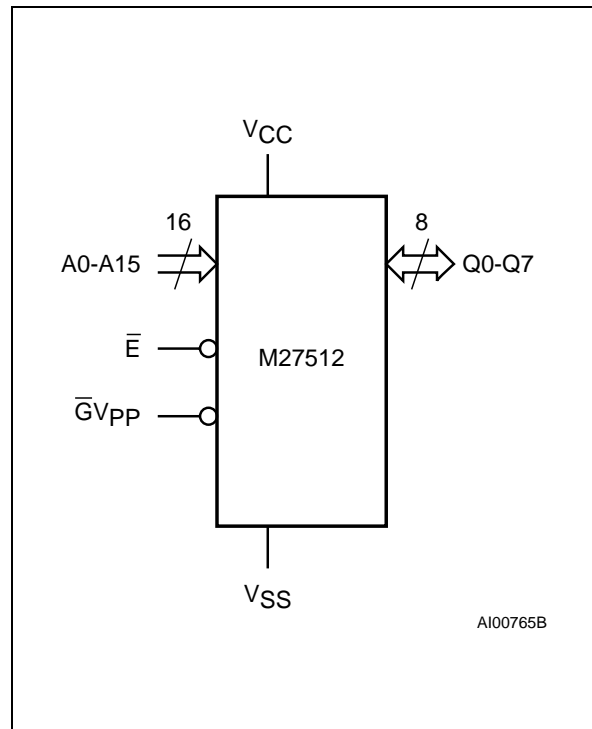
DESCRIPTION

The M27512 is a 524,288 bit UV erasable and electrically programmable memory EPROM. It is organized as 65,536 words by 8 bits.

The M27512 is housed in a 28 Pin Window Ceramic Frit-Seal Dual-in-Line package. The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written to the device by following the programming procedure.



Logic Diagram

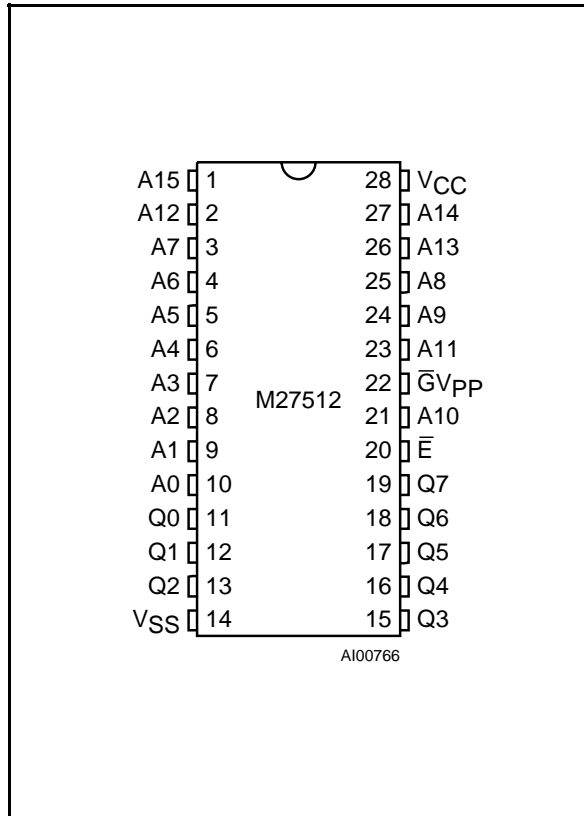


Signal Names

A0-A15	Address Inputs
Q0-Q7	Data Outputs
E	Chip Enable
$\bar{G}V_{PP}$	Output Enable / Program Supply
V _{CC}	Supply Voltage
V _{SS}	Ground

M27512

DIP Pin Connections



Ordering Information Scheme

For a list of available options or for further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

Example: M27512A -2 F 1

Speed and V _{CC} Tolerance	
-2	200ns, 5V±5%
blank	250ns, 5V±5%
-3	300ns, 5V±5%
-20	200ns, 5V±10%
-25	250ns, 5V±10%

Package	
F	FDIP28W

Temp. Range	
1	0 to 70 °C
6	-40 to 85 °C